

SEMiX453GD176HDc



SEMiX® 33c

Trench IGBT Modules

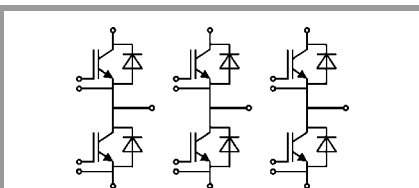
SEMiX453GD176HDc

Features

- Homogeneous Si
- Trench = Trenchgate technology
- $V_{CE(sat)}$ with positive temperature coefficient
- UL recognised file no. E63532

Typical Applications*

- AC inverter drives
- UPS
- Electronic welders



GD

Absolute Maximum Ratings				
Symbol	Conditions		Values	Unit
IGBT				
V _{CES}			1700	V
I _C	T _j = 150 °C	T _c = 25 °C	444	A
		T _c = 80 °C	315	A
I _{Cnom}			300	A
I _{CRM}	I _{CRM} = 2xI _{Cnom}		600	A
V _{GES}			-20 ... 20	V
t _{psc}	V _{CC} = 1000 V V _{GE} ≤ 20 V V _{CES} ≤ 1700 V	T _j = 125 °C	10	µs
T _j			-55 ... 150	°C
Inverse diode				
I _F	T _j = 150 °C	T _c = 25 °C	545	A
		T _c = 80 °C	365	A
I _{Fnom}			300	A
I _{FRM}	I _{FRM} = 2xI _{Fnom}		600	A
I _{FSM}	t _p = 10 ms, sin 180°, T _j = 25 °C		2900	A
T _j			-40 ... 150	°C
Module				
I _{t(RMS)}			600	A
T _{stg}			-40 ... 125	°C
V _{isol}	AC sinus 50Hz, t = 1 min		4000	V

Characteristics						
Symbol	Conditions		min.	typ.	max.	Unit
IGBT						
V _{CE(sat)}	I _C = 300 A	T _J = 25 °C		2	2.45	V
	V _{GE} = 15 V chipllevel	T _J = 125 °C		2.45	2.9	V
V _{CE0}		T _J = 25 °C		1	1.2	V
		T _J = 125 °C		0.9	1.1	V
r _{CE}	V _{GE} = 15 V	T _J = 25 °C		3.3	4.2	mΩ
		T _J = 125 °C		5.2	6.0	mΩ
V _{GE(th)}	V _{GE} =V _{CE} , I _C = 12 mA		5.2	5.8	6.4	V
I _{CES}	V _{GE} = 0 V	T _J = 25 °C			3	mA
	V _{CE} = 1700 V	T _J = 125 °C				mA
C _{ies}	V _{CE} = 25 V	f = 1 MHz		26.4		nF
C _{oes}	V _{GE} = 0 V	f = 1 MHz		1.10		nF
C _{res}		f = 1 MHz		0.88		nF
Q _G	V _{GE} = - 8 V...+ 15 V			2799		nC
R _{Gint}	T _J = 25 °C			2.50		Ω
t _{d(on)}	V _{CC} = 1200 V	T _J = 125 °C		335		ns
t _r	I _C = 300 A	T _J = 125 °C		70		ns
E _{on}	R _{G on} = 4.3 Ω	T _J = 125 °C		215		mJ
t _{d(off)}	R _{G off} = 4.3 Ω	T _J = 125 °C		990		ns
t _f		T _J = 125 °C		150		ns
E _{off}		T _J = 125 °C		125		mJ
R _{th(j-c)}	per IGBT				0.071	K/W



SEMiX® 33c

Trench IGBT Modules

SEMiX453GD176HDc

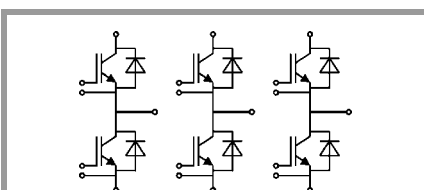
Features

- Homogeneous Si
- Trench = Trenchgate technology
- $V_{CE(sat)}$ with positive temperature coefficient
- UL recognised file no. E63532

Typical Applications*

- AC inverter drives
- UPS
- Electronic welders

Characteristics						
Symbol	Conditions		min.	typ.	max.	Unit
Inverse diode						
V _F = V _{EC}	I _F = 300 A V _{GE} = 0 V chip	T _j = 25 °C		1.5	1.70	V
		T _j = 125 °C		1.4	1.6	V
V _{F0}		T _j = 25 °C	0.9	1.1	1.3	V
		T _j = 125 °C	0.7	0.9	1.1	V
r _F		T _j = 25 °C	1.3	1.3	1.3	mΩ
		T _j = 125 °C	1.8	1.8	1.8	mΩ
I _{RRM}	I _F = 300 A di/dt _{off} = 4700 A/μs V _{GE} = -15 V V _{CC} = 1200 V	T _j = 125 °C		350		A
Q _{rr}		T _j = 125 °C		115		μC
E _{rr}		T _j = 125 °C		65		mJ
R _{th(j-c)}	per diode				0.11	K/W
Module						
L _{CE}				20		nH
R _{CC'+EE'}	res., terminal-chip	T _C = 25 °C		0.7		mΩ
		T _C = 125 °C		1		mΩ
R _{th(c-s)}	per module			0.014		K/W
M _s	to heat sink (M5)		3		5	Nm
M _t		to terminals (M6)	2.5		5	Nm
						Nm
w					900	g
Temperatur Sensor						
R ₁₀₀	T _C =100°C (R ₂₅ =5 kΩ)			493 ± 5%		Ω
B _{100/125}	R _(T) =R ₁₀₀ exp[B _{100/125} (1/T-1/T ₁₀₀)]; T[K];			3550 ±2%		K



GD

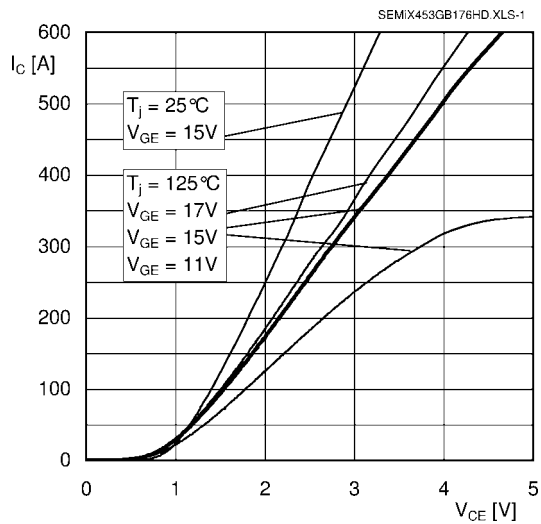


Fig. 1: Typ. output characteristic, inclusive $R_{CC'} + E_E$

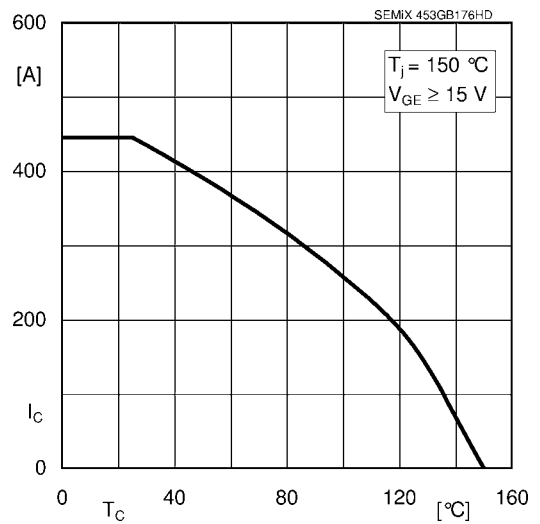


Fig. 2: Rated current vs. temperature $I_C = f(T_C)$

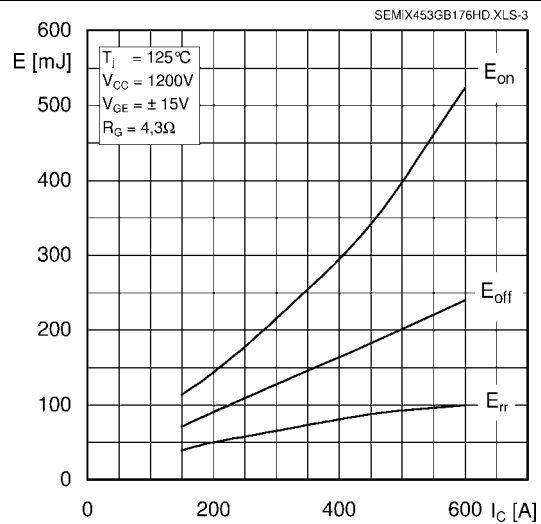


Fig. 3: Typ. turn-on /-off energy = $f(I_C)$

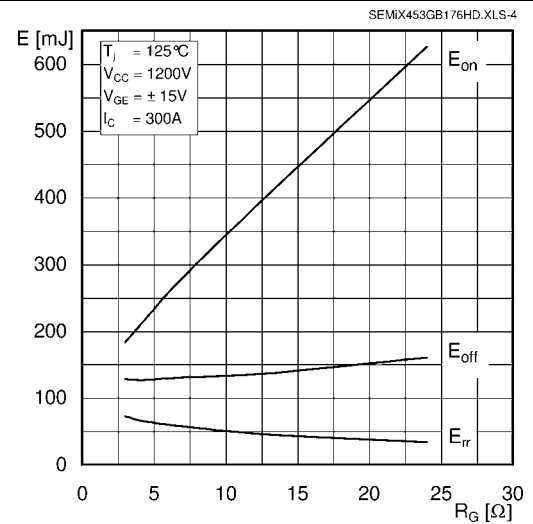


Fig. 4: Typ. turn-on /-off energy = $f(R_G)$

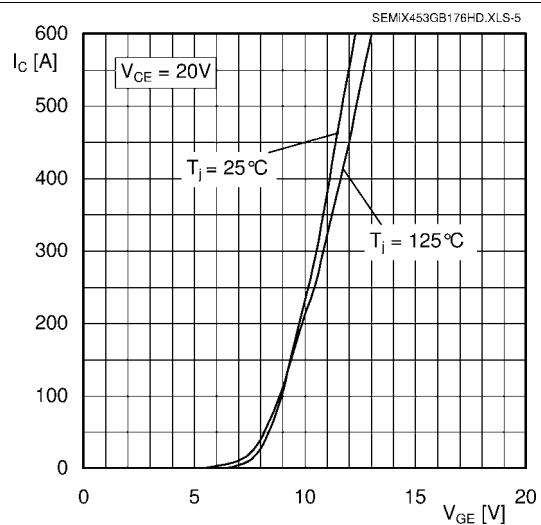


Fig. 5: Typ. transfer characteristic

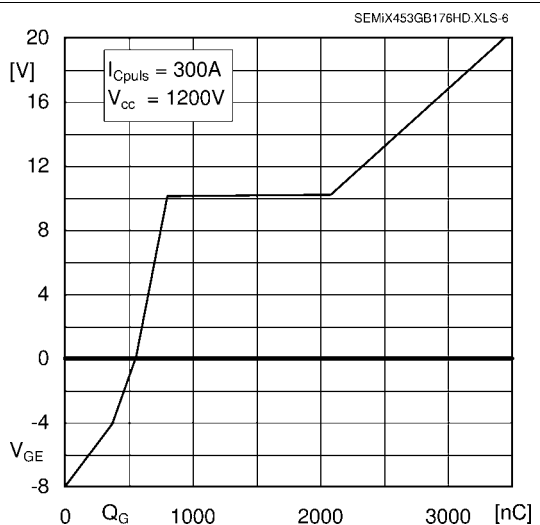
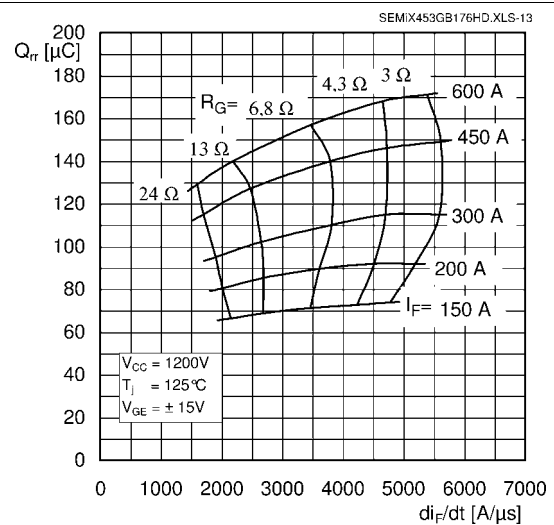
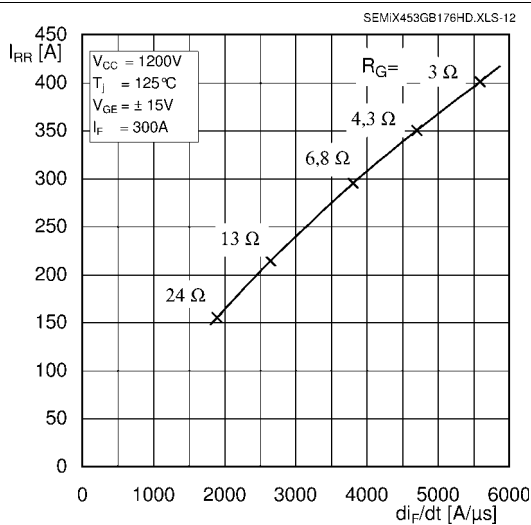
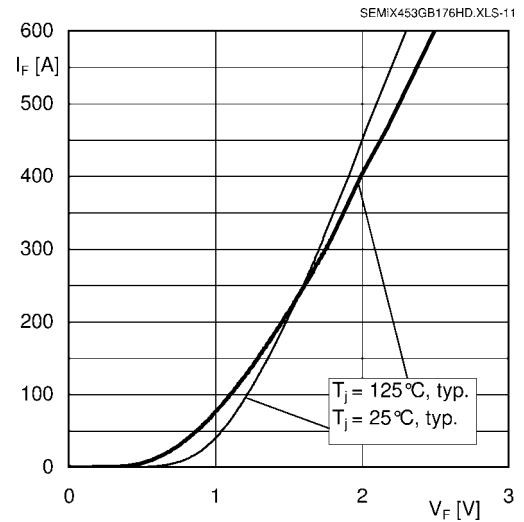
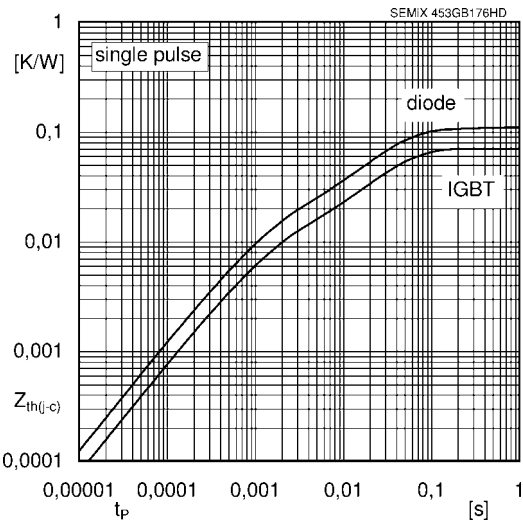
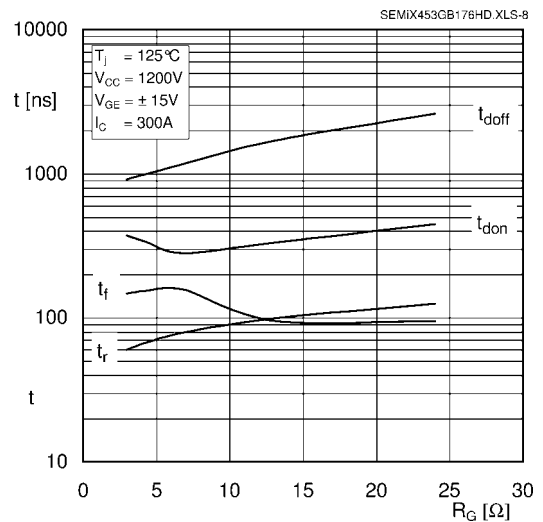
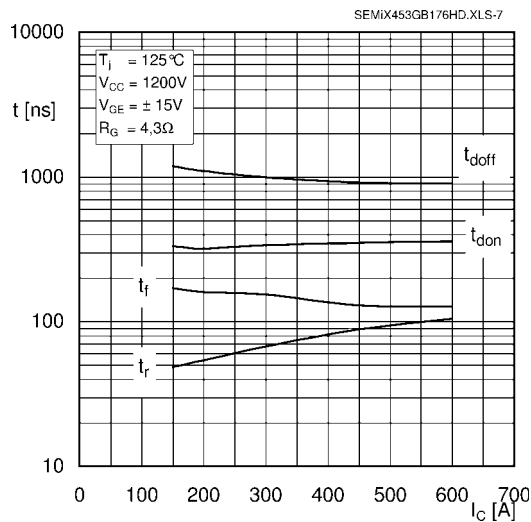
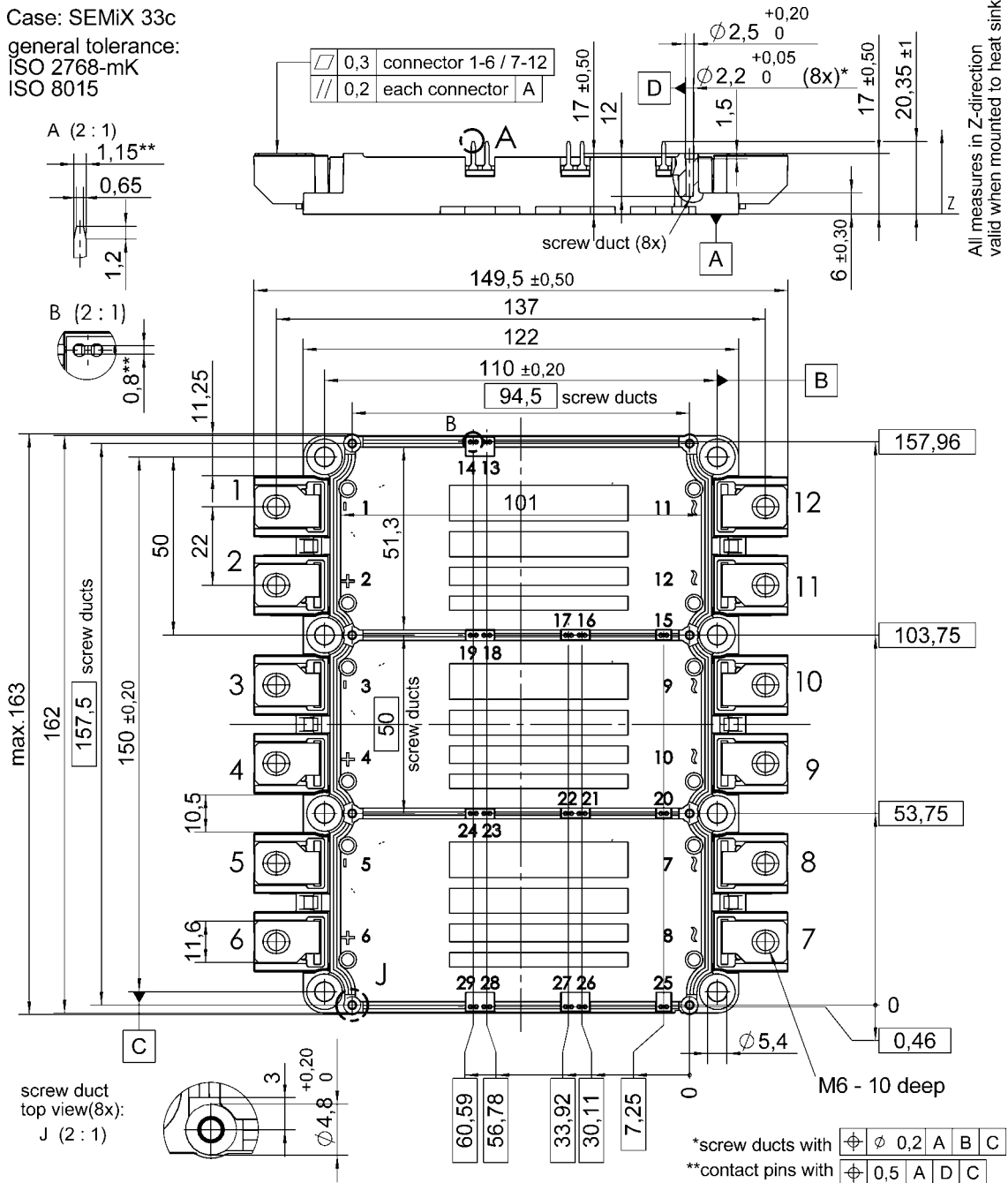


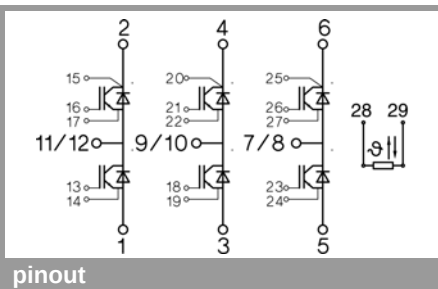
Fig. 6: Typ. gate charge characteristic



Case: SEMiX 33c
general tolerance:
ISO 2768-mk
ISO 8015



SEMiX 33c



This is an electrostatic discharge sensitive device (ESDS), international standard IEC 60747-1, Chapter IX

* The specifications of our components may not be considered as an assurance of component characteristics. Components have to be tested for the respective application. Adjustments may be necessary. The use of SEMIKRON products in life support appliances and systems is subject to prior specification and written approval by SEMIKRON. We therefore strongly recommend prior consultation of our personal.